

# Automotive N-Channel 40 V (D-S) 175 °C MOSFET

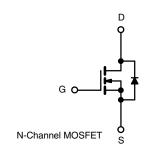
PRODUCT SUMMARY					
V <sub>DS</sub> (V)	40				
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS}$ = 10 V	0.0056				
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS}$ = 4.5 V	0.0070				
I <sub>D</sub> (A)	50				
Configuration	Single				
Package	TO-252				

# TO-252 Drain connected to tab

## FEATURES

- TrenchFET<sup>®</sup> power MOSFET
- · Package with low thermal resistance
- AEC-Q101 qualified
- 100 %  $\rm R_g$  and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_C = 25 \text{ °C}$ , unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V <sub>DS</sub>	40	V	
Gate-Source Voltage	V <sub>GS</sub>	± 20			
Continuous Drain Current	T <sub>C</sub> = 25 °C <sup>a</sup>	- I <sub>D</sub>	50		
	T <sub>C</sub> = 125 °C		45		
Continuous Source Current (Diode Conduction	I <sub>S</sub>	50	A		
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>		200	
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	33		
Single Pulse Avalanche Energy		E <sub>AS</sub>	54	mJ	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	- P <sub>D</sub>	71	w	
	T <sub>C</sub> = 125 °C		23		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount <sup>c</sup>	R <sub>thJA</sub>	50	°C/W	
Junction-to-Case (Drain)		R <sub>thJC</sub>	2.1	C/W	

#### Notes

a. Package limited.

b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

c. When mounted on 1" square PCB (FR4 material).

1

# SQD50N04-5m6L



Vishay Siliconix

PARAMETER	SYMBOL	rise noted) TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static		•						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 V, I_D = 250 \mu A$		40	-	-	v	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}$ , $I_D = 250 \ \mu A$		2.0	2.5		
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 100	nA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V	-	-	1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	$V_{DS} = 40 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	50	μA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 175 °C	-	-	150		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	50	-	-	Α	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A	-	0.0043	0.0056	Ω	
Durin Course On Otata Desistance a	Б	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C	-	-	0.0094		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 175 °C	-	-	0.0115		
		$V_{GS} = 4.5 V$	I <sub>D</sub> = 15 A	-	0.0057	0.0070		
Forward Transconductance b	<b>g</b> fs	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 15 A		-	100	-	S	
Dynamic <sup>b</sup>		·						
Input Capacitance	C <sub>iss</sub>			-	2850	4000		
Output Capacitance	C <sub>oss</sub> V <sub>G</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 25 V, f = 1 MHz	-	360	500	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	1		-	135	200		
Total Gate Charge <sup>c</sup>	Qg			-	46	75	nC	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 20 \text{ V}, I_{D} = 50 \text{ A}$	-	10	-		
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>	1		-	8	-		
Gate Resistance	Rg	f = 1 MHz		1.3	2.8	4.5	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	9	15	-	
Rise Time <sup>c</sup>	t <sub>r</sub>	$\label{eq:VDD} \begin{array}{l} V_{\text{DD}} = 20 \text{ V}, \ R_{\text{L}} = 0.4 \ \Omega \\ I_{\text{D}} \cong 50 \text{ A}, \ V_{\text{GEN}} = 10 \text{ V}, \ R_{\text{g}} = 1 \ \Omega \end{array}$		-	19	30	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	26	40		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	10	15		
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>	·			•			
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	200	Α	
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = 30 A, V <sub>GS</sub> = 0 V		-	0.87	1.5	V	

Notes

a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$ 

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

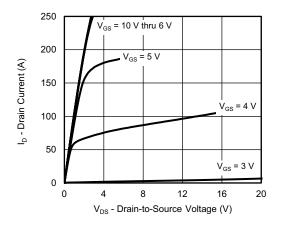
2



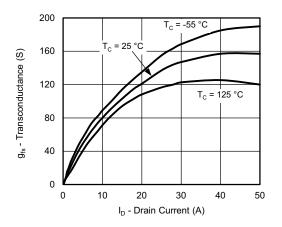
# SQD50N04-5m6L

Vishay Siliconix

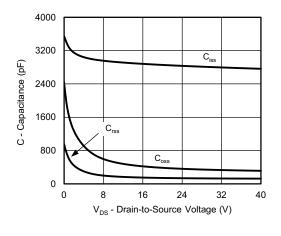
## TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



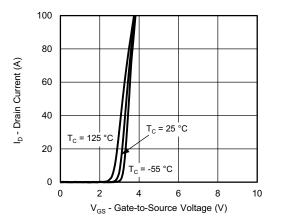
**Output Characteristics** 



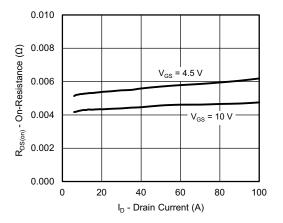
Transconductance



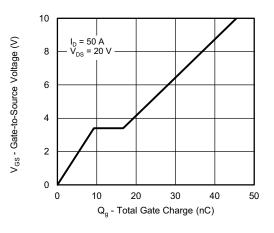
#### Capacitance



**Transfer Characteristics** 



**On-Resistance vs. Drain Current** 



**Gate Charge** 

S15-2665-Rev. A, 09-Nov-15

3

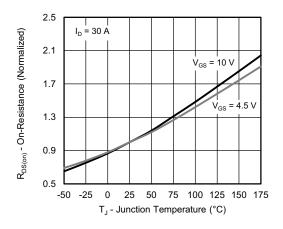
Document Number: 63413

For technical questions, contact: automostechsupport@vishay.com THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFI Downloaded From Oneyac.com w.vishay.com/doc?91000

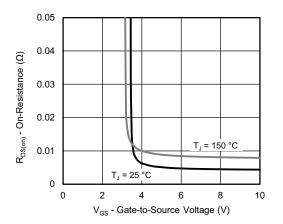




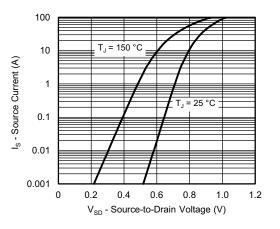
## **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



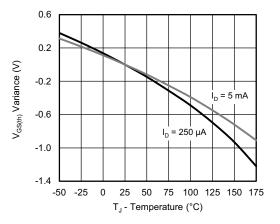
#### **On-Resistance vs. Junction Temperature**

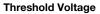


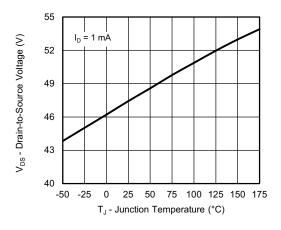
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage







Drain Source Breakdown vs. Junction Temperature

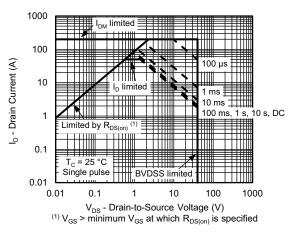
4



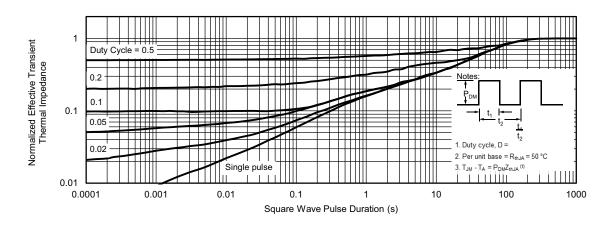
# SQD50N04-5m6L

**Vishay Siliconix** 

## **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



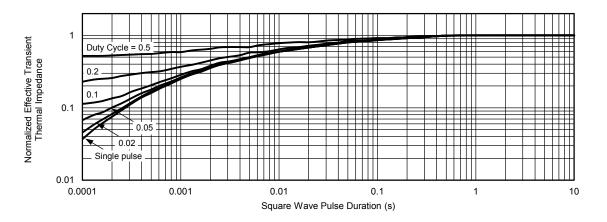
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



## **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

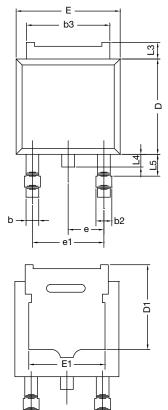
#### Note

- The characteristics shown in the two graphs
- Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction to Case (25 °C)

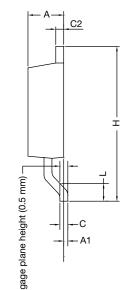
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <u>www.vishay.com/ppg?63413</u>.





# **TO-252AA Case Outline**



	MILLIN	IETERS	INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
А	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090 BSC		
e1	4.56	BSC	0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T13-0592-Rev. A, 02-Sep-13 DWG: 6019					

Note

• Dimension L3 is for reference only.

Ф **Т** 



## **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



Vishay

# Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.



单击下面可查看定价,库存,交付和生命周期等信息

>>Vishay(威世)

>>点击查看相关商品